TOSHIBA Transistor Silicon NPN Epitaxial Type

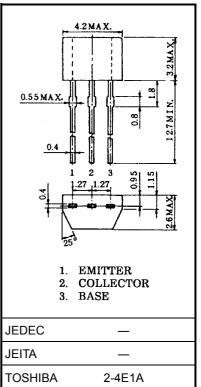
2SC3113

For Audio Amplifier and Switching Applications

- High DC current gain: hFE = 600~3600
- High breakdown voltage: $V_{CEO} = 50 \text{ V}$
- High collector current: IC = 150 mA (max)
- Small package

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Collector-base voltage	V _{CBO}	50	V	
Collector-emitter voltage	V _{CEO}	50	V	
Emitter-base voltage	V _{EBO}	5	V	
Collector current	Ι _C	150	mA	
Base current	Ι _Β	30	mA	
Collector power dissipation	P _C	200	mW	
Junction temperature	Tj	125	°C	
Storage temperature range	T _{stg}	-55~125	°C	



Weight: 0.13 g (typ.)

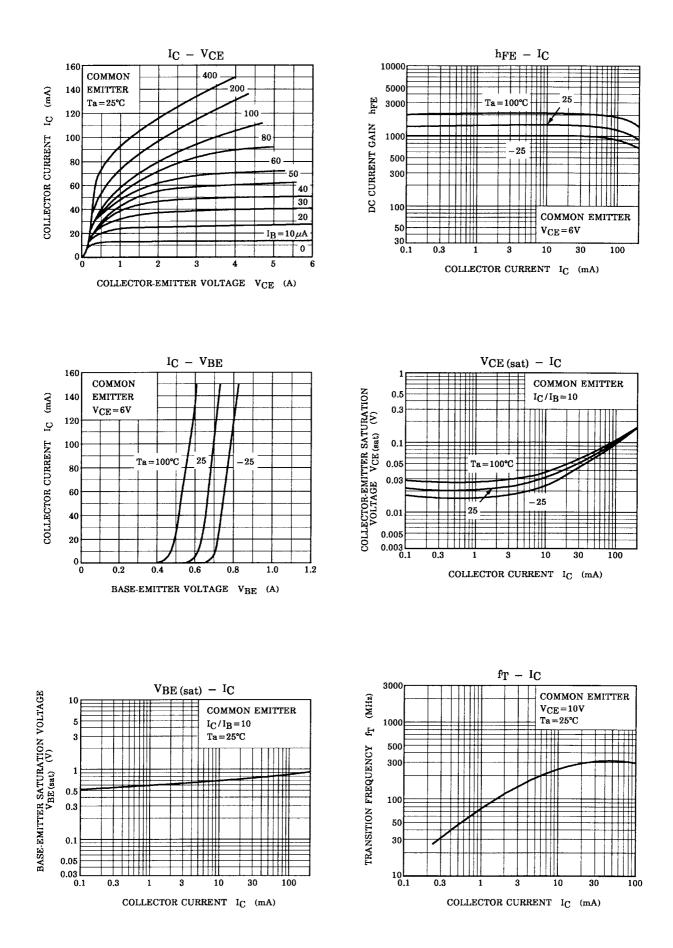
Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = 50 \text{ V}, \text{ I}_{E} = 0$	_	_	0.1	μA
Emitter cut-off current	I _{EBO}	$V_{EB} = 5 \text{ V}, \text{ I}_{C} = 0$	_	_	0.1	μA
DC current gain	h _{FE} (Note)	$V_{CE} = 6 V, I_{C} = 2 mA$	600	_	3600	
Collector-emitter saturation voltage	V _{CE (sat)}	$I_{C} = 100 \text{ mA}, I_{B} = 10 \text{ mA}$	_	0.12	0.25	V
Transition frequency	fT	$V_{CE} = 10 \text{ V}, I_{C} = 10 \text{ mA}$	100	250	_	MHz
Collector output capacitance	C _{ob}	$V_{CB} = 10 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1 \text{ MHz}$	_	3.5		pF
Noise figure	NF (1)	V_{CE} = 6 V, I_C = 0.1 mA, f = 100 Hz, R_G = 10 $k\Omega$	_	0.5	_	dB
	NF (2)	V_{CE} = 6 V, I _C = 0.1 mA, f = 1 kHz, R_{G} = 10 $k\Omega$	_	0.3	_	

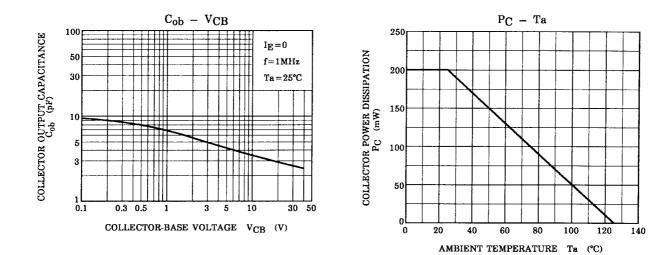
Note: hFE classification A: 600~1800, B: 1200~3600

Unit: mm

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